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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Not For New Designs
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	100MHz
Connectivity	CANbus, EBI/EMI, I ² C, IrDA, SD, SPI, UART/USART, USB, USB OTG
Peripherals	DMA, I ² S, LVD, POR, PWM, WDT
Number of I/O	100
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 42x16b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LBGA
Supplier Device Package	144-MAPBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk20dx256zvm10

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Terminology and guidelines

Field	Description	Values
FFF	Program flash memory size	• 32 = 32 KB • 64 = 64 KB • 128 = 128 KB • 256 = 256 KB • 512 = 512 KB • 1M0 = 1 MB • 2M0 = 2 MB
R	Silicon revision	• Z = Initial • (Blank) = Main • A = Revision after main
T	Temperature range (°C)	• V = -40 to 105 • C = -40 to 85
PP	Package identifier	• FM = 32 QFN (5 mm x 5 mm) • FT = 48 QFN (7 mm x 7 mm) • LF = 48 LQFP (7 mm x 7 mm) • LH = 64 LQFP (10 mm x 10 mm) • MP = 64 MAPBGA (5 mm x 5 mm) • LK = 80 LQFP (12 mm x 12 mm) • LL = 100 LQFP (14 mm x 14 mm) • MC = 121 MAPBGA (8 mm x 8 mm) • LQ = 144 LQFP (20 mm x 20 mm) • MD = 144 MAPBGA (13 mm x 13 mm) • MJ = 256 MAPBGA (17 mm x 17 mm)
CC	Maximum CPU frequency (MHz)	• 5 = 50 MHz • 7 = 72 MHz • 10 = 100 MHz • 12 = 120 MHz • 15 = 150 MHz
N	Packaging type	• R = Tape and reel • (Blank) = Trays

2.4 Example

This is an example part number:

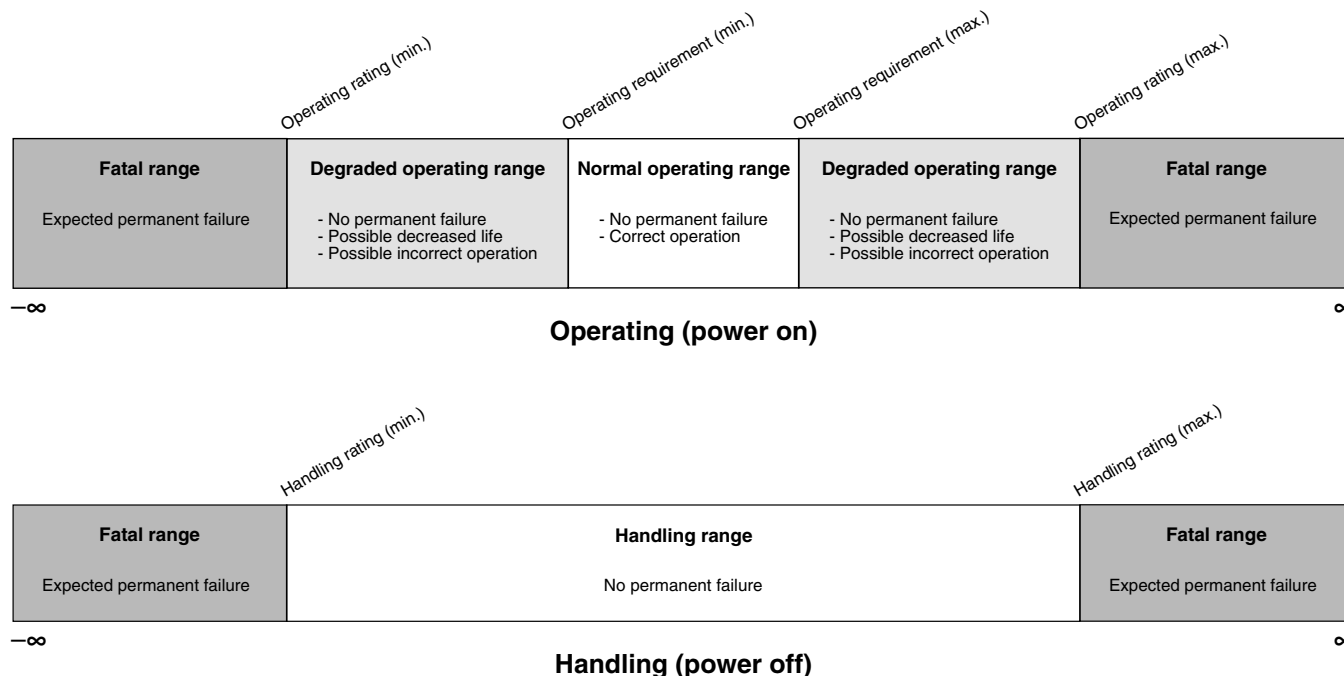
MK20DN512ZVMD10

3 Terminology and guidelines

3.1 Definition: Operating requirement

An *operating requirement* is a specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip.

3.6 Relationship between ratings and operating requirements



3.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

3.8 Definition: Typical value

A *typical value* is a specified value for a technical characteristic that:

- Lies within the range of values specified by the operating behavior
- Given the typical manufacturing process, is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions

Typical values are provided as design guidelines and are neither tested nor guaranteed.

5.2 Nonswitching electrical specifications

5.2.1 Voltage and current operating requirements

Table 1. Voltage and current operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	3.6	V	
V_{DDA}	Analog supply voltage	1.71	3.6	V	
$V_{DD} - V_{DDA}$	V_{DD} -to- V_{DDA} differential voltage	-0.1	0.1	V	
$V_{SS} - V_{SSA}$	V_{SS} -to- V_{SSA} differential voltage	-0.1	0.1	V	
V_{BAT}	RTC battery supply voltage	1.71	3.6	V	
V_{IH}	Input high voltage $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ $1.7\text{ V} \leq V_{DD} \leq 2.7\text{ V}$	$0.7 \times V_{DD}$	—	V	
		$0.75 \times V_{DD}$	—	V	
V_{IL}	Input low voltage $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ $1.7\text{ V} \leq V_{DD} \leq 2.7\text{ V}$	—	$0.35 \times V_{DD}$	V	
		—	$0.3 \times V_{DD}$	V	
V_{HYS}	Input hysteresis	$0.06 \times V_{DD}$	—	V	
I_{ICDIO}	Digital pin negative DC injection current — single pin $V_{IN} < V_{SS}-0.3\text{V}$	-5	—	mA	1
I_{ICAO}	Analog ² , EXTAL, and XTAL pin DC injection current — single pin $V_{IN} < V_{SS}-0.3\text{V}$ (Negative current injection) $V_{IN} > V_{DD}+0.3\text{V}$ (Positive current injection)	-5	—	mA	3
		—	+5		
I_{ICcont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins - Negative current injection - Positive current injection	-25	—	mA	
		—	+25		
V_{ODPU}	Open drain pullup voltage level	V_{DD}	V_{DD}	V	4
V_{RAM}	V_{DD} voltage required to retain RAM	1.2	—	V	
V_{RFVBAT}	V_{BAT} voltage required to retain the VBAT register file	V_{POR_VBAT}	—	V	

1. All 5 V tolerant digital I/O pins are internally clamped to V_{SS} through an ESD protection diode. There is no diode connection to V_{DD} . If V_{IN} is less than V_{DIO_MIN} , a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{DIO_MIN}-V_{IN})/|I_{ICDIO}|$.
2. Analog pins are defined as pins that do not have an associated general purpose I/O port function. Additionally, EXTAL and XTAL are analog pins.
3. All analog pins are internally clamped to V_{SS} and V_{DD} through ESD protection diodes. If V_{IN} is less than V_{AIO_MIN} or greater than V_{AIO_MAX} , a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{AIO_MIN}-V_{IN})/|I_{ICAO}|$. The positive injection current limiting resistor is calculated as $R=(V_{IN}-V_{AIO_MAX})/|I_{ICAO}|$. Select the larger of these two calculated resistances if the pin is exposed to positive and negative injection currents.
4. Open drain outputs must be pulled to V_{DD} .

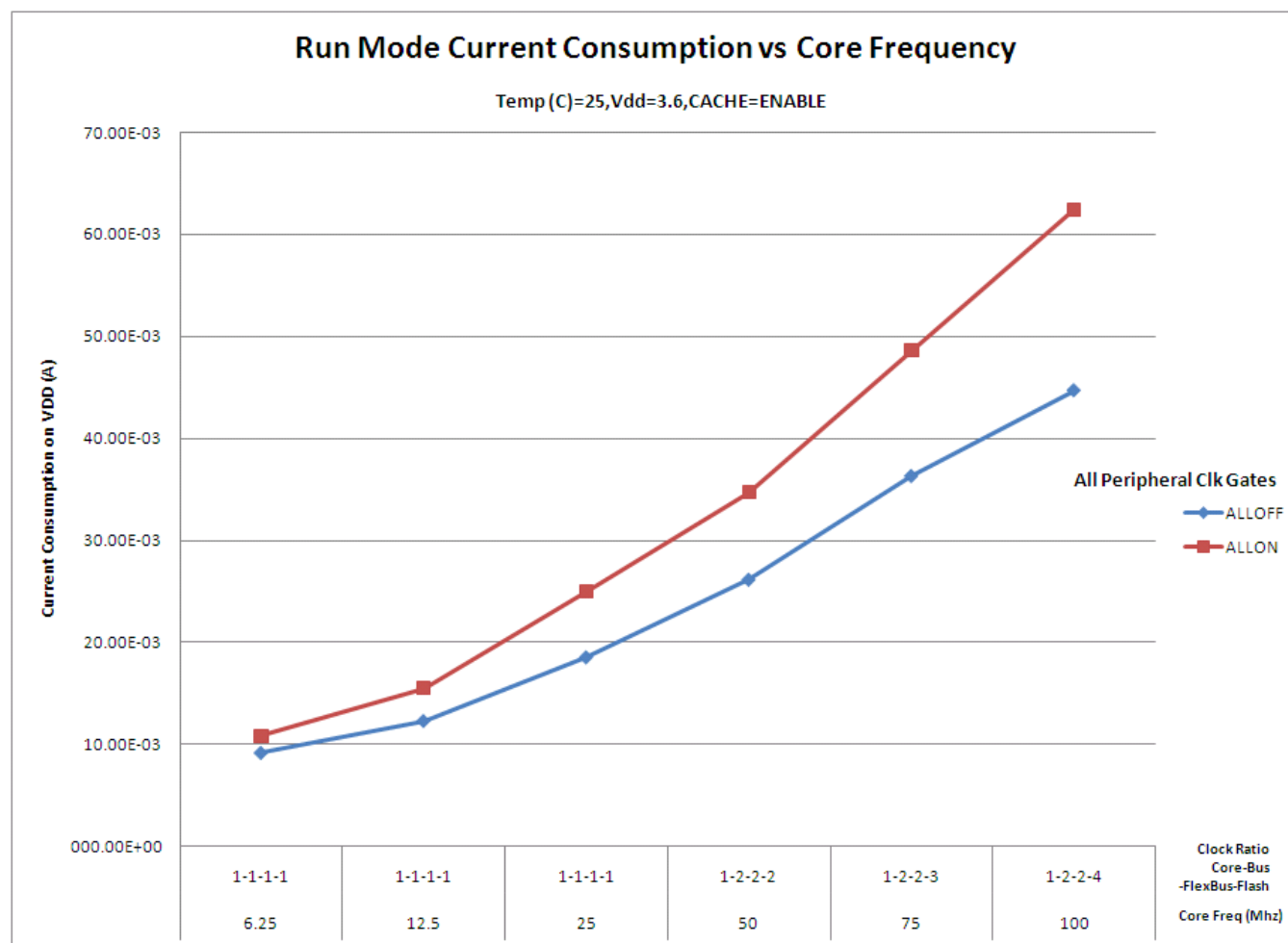


Figure 2. Run mode supply current vs. core frequency

5.2.6 EMC radiated emissions operating behaviors

Table 7. EMC radiated emissions operating behaviors as measured on 144LQFP and 144MAPBGA packages

Symbol	Description	Frequency band (MHz)	144LQFP	144MAPBGA	Unit	Notes
V _{RE1}	Radiated emissions voltage, band 1	0.15–50	23	12	dBμV	1, 2
V _{RE2}	Radiated emissions voltage, band 2	50–150	27	24	dBμV	
V _{RE3}	Radiated emissions voltage, band 3	150–500	28	27	dBμV	
V _{RE4}	Radiated emissions voltage, band 4	500–1000	14	11	dBμV	
V _{RE_IEC}	IEC level	0.15–1000	K	K	—	2, 3

1. Determined according to IEC Standard 61967-1, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions* and IEC Standard 61967-2, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*. Measurements were made while the microcontroller was running basic application code. The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.

Table 14. JTAG full voltage range electricals (continued)

Symbol	Description	Min.	Max.	Unit
J3	TCLK clock pulse width			
	• Boundary Scan	50	—	ns
	• JTAG and CJTAG	25	—	ns
	• Serial Wire Debug	12.5	—	ns
J4	TCLK rise and fall times	—	3	ns
J5	Boundary scan input data setup time to TCLK rise	20	—	ns
J6	Boundary scan input data hold time after TCLK rise	0	—	ns
J7	TCLK low to boundary scan output data valid	—	25	ns
J8	TCLK low to boundary scan output high-Z	—	25	ns
J9	TMS, TDI input data setup time to TCLK rise	8	—	ns
J10	TMS, TDI input data hold time after TCLK rise	1.4	—	ns
J11	TCLK low to TDO data valid	—	22.1	ns
J12	TCLK low to TDO high-Z	—	22.1	ns
J13	TRST assert time	100	—	ns
J14	TRST setup time (negation) to TCLK high	8	—	ns

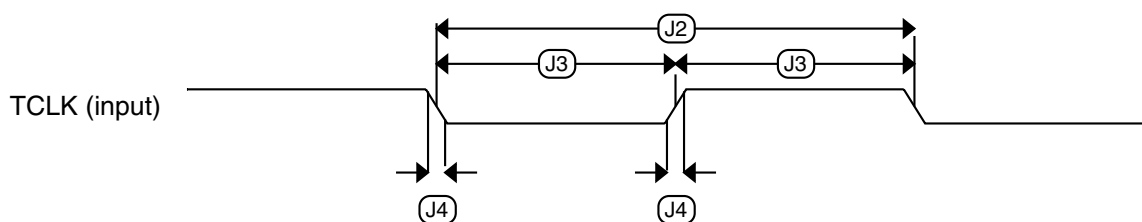
**Figure 5. Test clock input timing**

Table 21. Flash command timing specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{pgmchk}	Program Check execution time	—	—	45	μs	1
t_{rdsrc}	Read Resource execution time	—	—	30	μs	1
t_{pgm4}	Program Longword execution time	—	65	145	μs	
$t_{ersblk256k}$	Erase Flash Block execution time • 256 KB program/data flash	—	435	3700	ms	2
t_{ersscr}	Erase Flash Sector execution time	—	14	114	ms	2
$t_{pgmsec512}$	Program Section execution time • 512 bytes flash	—	2.4	—	ms	
$t_{pgmsec1k}$	• 1 KB flash	—	4.7	—	ms	
$t_{pgmsec2k}$	• 2 KB flash	—	9.3	—	ms	
t_{rd1all}	Read 1s All Blocks execution time	—	—	1.8	ms	
t_{rdonce}	Read Once execution time	—	—	25	μs	1
$t_{pgmonce}$	Program Once execution time	—	65	—	μs	
t_{ersall}	Erase All Blocks execution time	—	870	7400	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	μs	1
$t_{swapx01}$	Swap Control execution time • control code 0x01	—	200	—	μs	
$t_{swapx02}$	• control code 0x02	—	70	150	μs	
$t_{swapx04}$	• control code 0x04	—	70	150	μs	
$t_{swapx08}$	• control code 0x08	—	—	30	μs	

1. Assumes 25 MHz flash clock frequency.

2. Maximum times for erase parameters based on expectations at cycling end-of-life.

6.4.1.3 Flash high voltage current behaviors

Table 22. Flash high voltage current behaviors

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DD_PGM}	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
I_{DD_ERS}	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

6.4.1.4 Reliability specifications

Table 23. NVM reliability specifications

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
Program Flash						

Table continues on the next page...

2. Specification is valid for all FB_AD[31:0] and $\overline{\text{FB_TA}}$.

Table 26. Flexbus full voltage range switching specifications

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	1.71	3.6	V	
	Frequency of operation	—	FB_CLK	MHz	
FB1	Clock period	1/FB_CLK	—	ns	
FB2	Address, data, and control output valid	—	13.5	ns	1
FB3	Address, data, and control output hold	0	—	ns	1
FB4	Data and $\overline{\text{FB_TA}}$ input setup	13.7	—	ns	2
FB5	Data and $\overline{\text{FB_TA}}$ input hold	0.5	—	ns	2

1. Specification is valid for all FB_AD[31:0], $\overline{\text{FB_BE/BWEn}}$, $\overline{\text{FB_CSn}}$, $\overline{\text{FB_OE}}$, FB_R/W, $\overline{\text{FB_TBST}}$, FB_TSI[1:0], FB_ALE, and $\overline{\text{FB_TS}}$.
2. Specification is valid for all FB_AD[31:0] and $\overline{\text{FB_TA}}$.

Table 30. 16-bit ADC with PGA characteristics (continued)

Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
G	Gain ⁴	- PGAG=0 - PGAG=1 - PGAG=2 - PGAG=3 - PGAG=4 - PGAG=5 - PGAG=6	0.95 1.9 3.8 7.6 15.2 30.0 58.8	1 2 4 8 16 31.6 63.3	1.05 2.1 4.2 8.4 16.6 33.2 67.8		R _{AS} < 100Ω
BW	Input signal bandwidth	16-bit modes < 16-bit modes	— —	— —	4 40	kHz kHz	
PSRR	Power supply rejection ratio	Gain=1	—	-84	—	dB	V _{DDA} = 3V ±100mV, f _{VDDA} = 50Hz, 60Hz
CMRR	Common mode rejection ratio	- Gain=1 - Gain=64	— —	-84 -85	— —	dB dB	V _{CM} = 500mVpp, f _{VCM} = 50Hz, 100Hz
V _{OFS}	Input offset voltage		—	0.2	—	mV	Output offset = V _{OFS} *(Gain+1)
T _{GSW}	Gain switching settling time		—	—	10	μs	5
E _{IL}	Input leakage error	All modes	I _{in} × R _{AS}			mV	I _{in} = leakage current (refer to the MCU's voltage and current operating ratings)
V _{PP,DIFF}	Maximum differential input signal swing		$\left(\frac{(\min(V_X, V_{DDA} - V_X) - 0.2) \times 4}{\text{Gain}} \right)$ where V _X = V _{REFPGA} × 0.583			V	6
SNR	Signal-to-noise ratio	- Gain=1 - Gain=64	80 52	90 66	— —	dB dB	16-bit differential mode, Average=32
THD	Total harmonic distortion	- Gain=1 - Gain=64	85 49	100 95	— —	dB dB	16-bit differential mode, Average=32, f _{in} =100Hz
SFDR	Spurious free dynamic range	- Gain=1 - Gain=64	85 53	105 88	— —	dB dB	16-bit differential mode, Average=32, f _{in} =100Hz

Table continues on the next page...

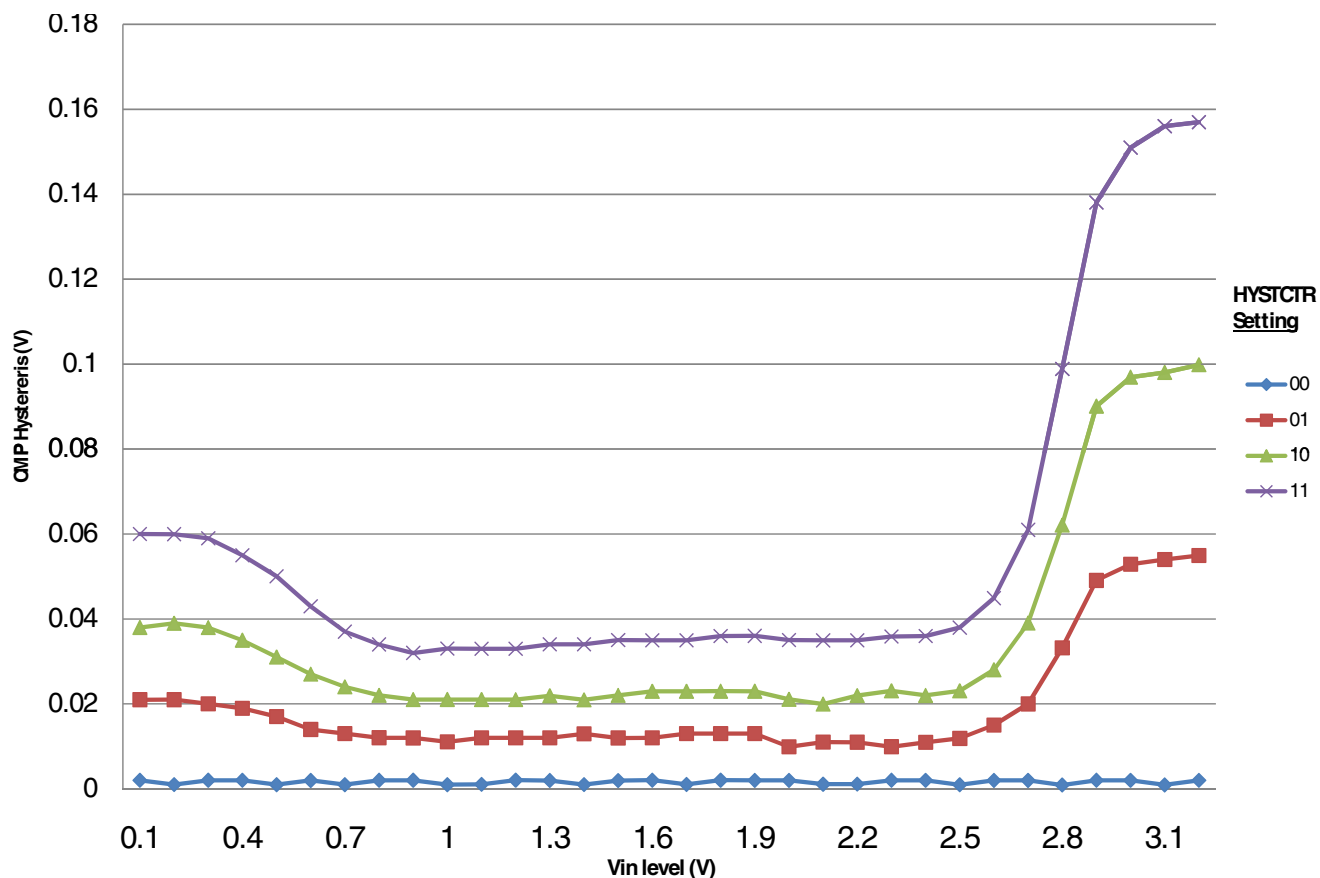


Figure 16. Typical hysteresis vs. Vin level (VDD=3.3V, PMODE=1)

6.6.3 12-bit DAC electrical characteristics

6.6.3.1 12-bit DAC operating requirements

Table 32. 12-bit DAC operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage	1.71	3.6	V	
V_{DACR}	Reference voltage	1.13	3.6	V	1
T_A	Temperature	Operating temperature range of the device		°C	
C_L	Output load capacitance	—	100	pF	2
I_L	Output load current	—	1	mA	

1. The DAC reference can be selected to be V_{DDA} or the voltage output of the VREF module (VREF_OUT)
2. A small load capacitance (47 pF) can improve the bandwidth performance of the DAC

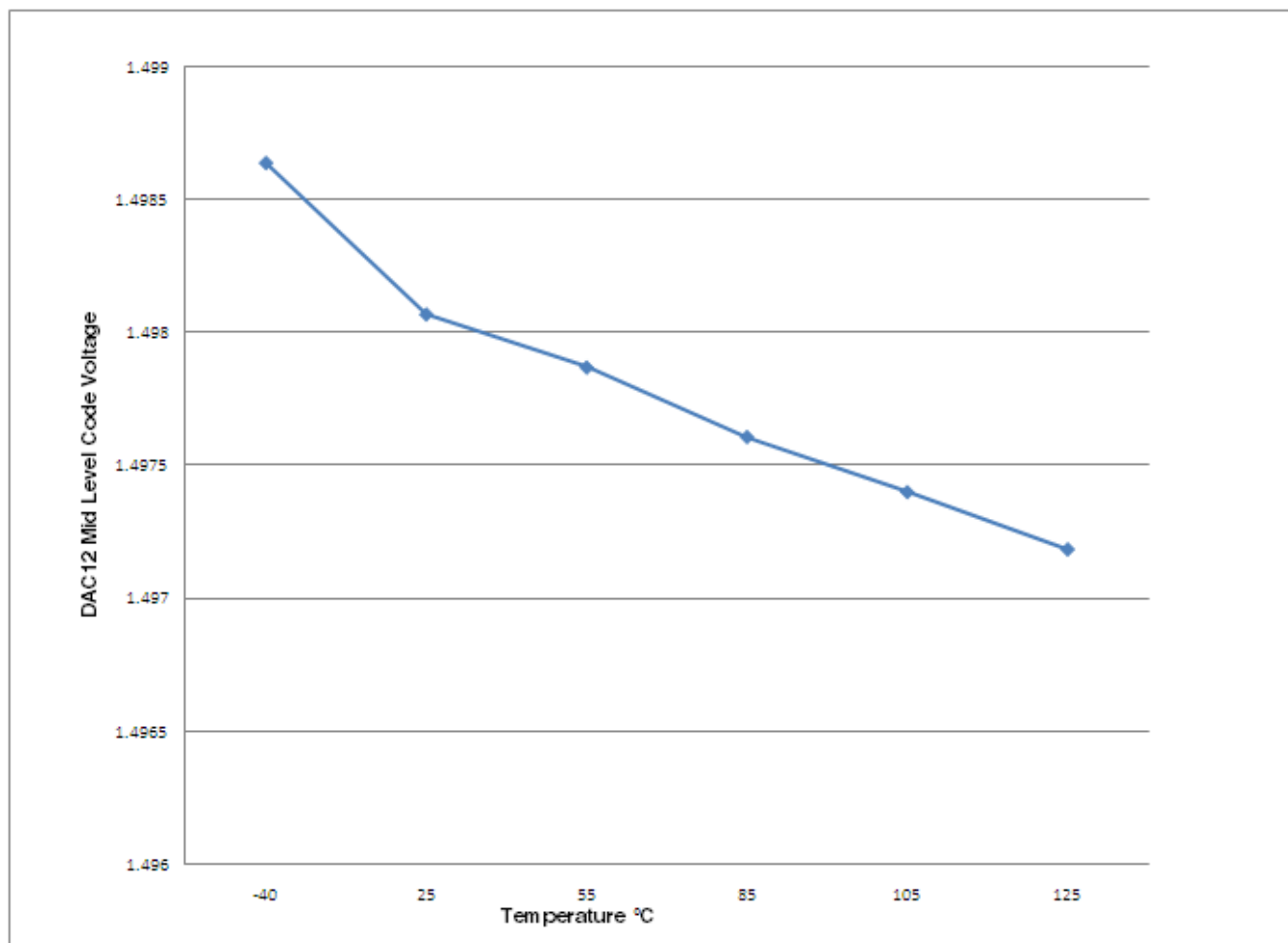


Figure 18. Offset at half scale vs. temperature

6.6.4 Voltage reference electrical specifications

Table 34. VREF full-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V _{DDA}	Supply voltage	1.71	3.6	V	
T _A	Temperature	Operating temperature range of the device		°C	
C _L	Output load capacitance	100		nF	1, 2

1. C_L must be connected to VREF_OUT if the VREF_OUT functionality is being used for either an internal or external reference.
2. The load capacitance should not exceed +/-25% of the nominal specified C_L value over the operating temperature range of the device.

Table 35. VREF full-range operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{out}	Voltage reference output with factory trim at nominal V_{DDA} and temperature=25C	1.1915	1.195	1.1977	V	
V_{out}	Voltage reference output — factory trim	1.1584	—	1.2376	V	
V_{step}	Voltage reference trim step	—	0.5	—	mV	
V_{tdrift}	Temperature drift ($V_{max} - V_{min}$ across the full temperature range)	—	—	80	mV	
I_{bg}	Bandgap only current	—	—	80	μA	1
I_{lp}	Low-power buffer current	—	—	360	μA	1
I_{hp}	High-power buffer current	—	—	1	mA	1
ΔV_{LOAD}	Load regulation				mV	1, 2
	• current = + 1.0 mA	—	2	—		
	• current = - 1.0 mA	—	5	—		
T_{stup}	Buffer startup time	—	—	100	μs	
V_{vdift}	Voltage drift ($V_{max} - V_{min}$ across the full voltage range)	—	2	—	mV	1

1. See the chip's Reference Manual for the appropriate settings of the VREF Status and Control register.
2. Load regulation voltage is the difference between the VREF_OUT voltage with no load vs. voltage with defined load

Table 36. VREF limited-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
T_A	Temperature	0	50	$^{\circ}C$	

Table 37. VREF limited-range operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V_{out}	Voltage reference output with factory trim	1.173	1.225	V	

6.7 Timers

See [General switching specifications](#).

6.8 Communication interfaces

**Table 39. USB VREG electrical specifications
(continued)**

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
I _{LIM}	Short circuit current	—	290	—	mA	

1. Typical values assume VREGIN = 5.0 V, Temp = 25 °C unless otherwise stated.

2. Operating in pass-through mode: regulator output voltage equal to the input voltage minus a drop proportional to I_{Load}.

6.8.4 CAN switching specifications

See [General switching specifications](#).

6.8.5 DSPI switching specifications (limited voltage range)

The DMA Serial Peripheral Interface (DSPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The tables below provide DSPI timing characteristics for classic SPI timing modes. Refer to the DSPI chapter of the Reference Manual for information on the modified transfer formats used for communicating with slower peripheral devices.

Table 40. Master mode DSPI timing (limited voltage range)

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	2.7	3.6	V	
	Frequency of operation	—	25	MHz	
DS1	DSPI_SCK output cycle time	$2 \times t_{\text{BUS}}$	—	ns	
DS2	DSPI_SCK output high/low time	$(t_{\text{SCK}}/2) - 2$	$(t_{\text{SCK}}/2) + 2$	ns	
DS3	DSPI_PCS _n valid to DSPI_SCK delay	$(t_{\text{BUS}} \times 2) - 2$	—	ns	1
DS4	DSPI_SCK to DSPI_PCS _n invalid delay	$(t_{\text{BUS}} \times 2) - 2$	—	ns	2
DS5	DSPI_SCK to DSPI_SOUT valid	—	8.5	ns	
DS6	DSPI_SCK to DSPI_SOUT invalid	-2	—	ns	
DS7	DSPI_SIN to DSPI_SCK input setup	15	—	ns	
DS8	DSPI_SCK to DSPI_SIN input hold	0	—	ns	

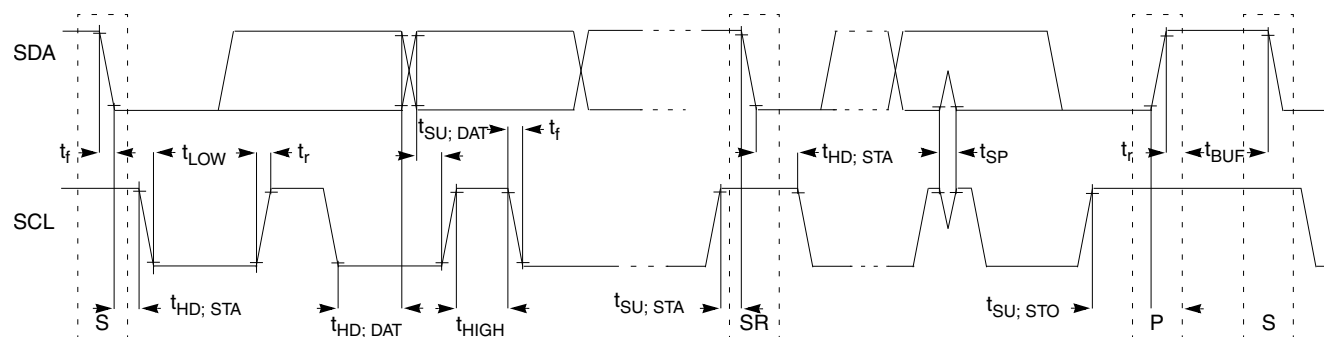
1. The delay is programmable in SPIx_CTARn[PSSCK] and SPIx_CTARn[CSSCK].

2. The delay is programmable in SPIx_CTARn[PASC] and SPIx_CTARn[ASC].

Table 44. I²C timing (continued)

Characteristic	Symbol	Standard Mode		Fast Mode		Unit
		Minimum	Maximum	Minimum	Maximum	
Fall time of SDA and SCL signals	t_f	—	300	$20 + 0.1C_b^5$	300	ns
Set-up time for STOP condition	$t_{SU; STO}$	4	—	0.6	—	μs
Bus free time between STOP and START condition	t_{BUF}	4.7	—	1.3	—	μs
Pulse width of spikes that must be suppressed by the input filter	t_{SP}	N/A	N/A	0	50	ns

1. The master mode I²C deasserts ACK of an address byte simultaneously with the falling edge of SCL. If no slaves acknowledge this address byte, then a negative hold time can result, depending on the edge rates of the SDA and SCL lines.
2. The maximum t_{HD; DAT} must be met only if the device does not stretch the LOW period (t_{LOW}) of the SCL signal.
3. Input signal Slew = 10ns and Output Load = 50pf
4. Set-up time in slave-transmitter mode is 1 IPBus clock period, if the TX FIFO is empty.
5. A Fast mode I²C bus device can be used in a Standard mode I²C bus system, but the requirement $t_{SU; DAT} \geq 250$ ns must then be met. This is automatically the case if the device does not stretch the LOW period of the SCL signal. If such a device does stretch the LOW period of the SCL signal, then it must output the next data bit to the SDA line $t_{rmax} + t_{SU; DAT} = 1000 + 250 = 1250$ ns (according to the Standard mode I²C bus specification) before the SCL line is released.
6. C_b = total capacitance of the one bus line in pF.

**Figure 23. Timing definition for fast and standard mode devices on the I²C bus**

6.8.8 UART switching specifications

See [General switching specifications](#).

6.8.10 I²S switching specifications

This section provides the AC timings for the I²S in master (clocks driven) and slave modes (clocks input). All timings are given for non-inverted serial clock polarity (TCR[TSCKP] = 0, RCR[RSCKP] = 0) and a non-inverted frame sync (TCR[TFSI] = 0, RCR[RFSI] = 0). If the polarity of the clock and/or the frame sync have been inverted, all the timings remain valid by inverting the clock signal (I2S_BCLK) and/or the frame sync (I2S_FS) shown in the figures below.

Table 46. I²S master mode timing (limited voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
S1	I2S_MCLK cycle time	$2 \times t_{SYS}$		ns
S2	I2S_MCLK pulse width high/low	45%	55%	MCLK period
S3	I2S_BCLK cycle time	$5 \times t_{SYS}$	—	ns
S4	I2S_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_BCLK to I2S_FS output valid	—	15	ns
S6	I2S_BCLK to I2S_FS output invalid	-2.5	—	ns
S7	I2S_BCLK to I2S_TXD valid	—	15	ns
S8	I2S_BCLK to I2S_TXD invalid	-3	—	ns
S9	I2S_RXD/I2S_FS input setup before I2S_BCLK	20	—	ns
S10	I2S_RXD/I2S_FS input hold after I2S_BCLK	0	—	ns

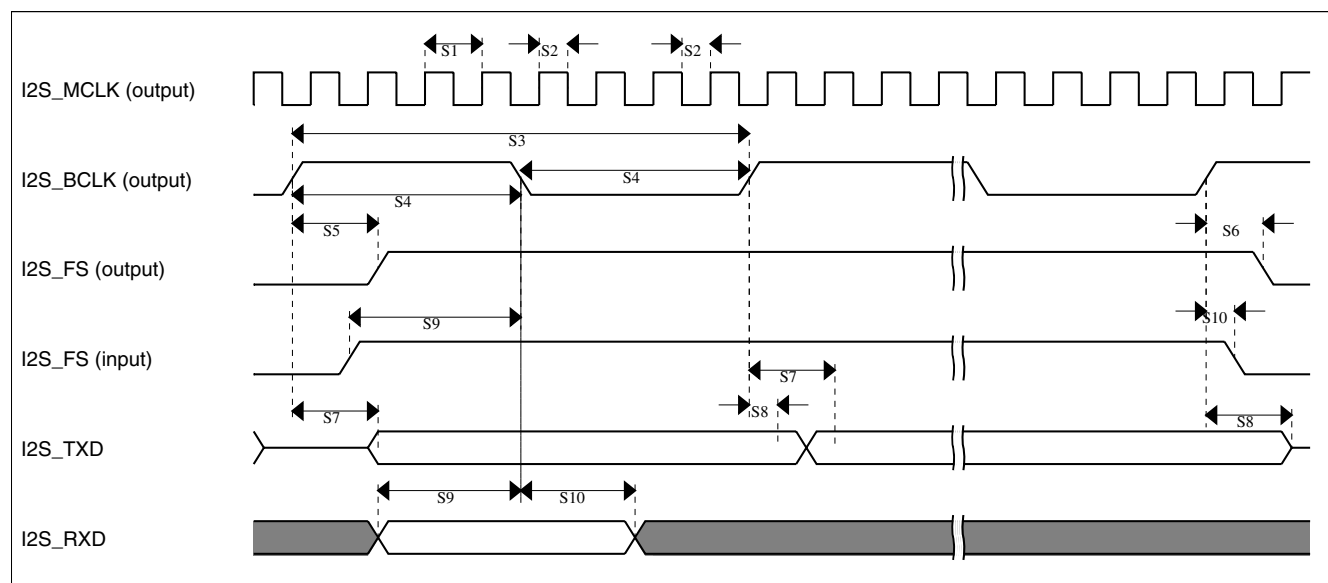
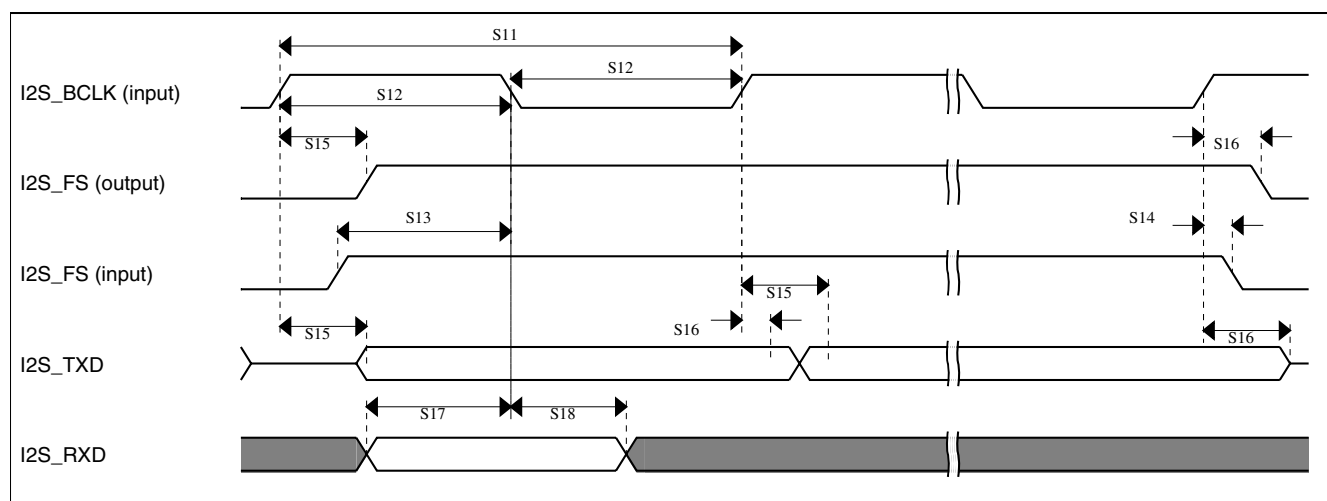


Figure 25. I²S timing — master mode

Table 47. I²S slave mode timing (limited voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
S11	I2S_BCLK cycle time (input)	$8 \times t_{\text{SYS}}$	—	ns
S12	I2S_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_FS input setup before I2S_BCLK	10	—	ns
S14	I2S_FS input hold after I2S_BCLK	3	—	ns
S15	I2S_BCLK to I2S_TXD/I2S_FS output valid	—	20	ns
S16	I2S_BCLK to I2S_TXD/I2S_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_BCLK	10	—	ns
S18	I2S_RXD hold after I2S_BCLK	2	—	ns

**Figure 26. I²S timing — slave modes****Table 48. I²S master mode timing (full voltage range)**

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	I2S_MCLK cycle time	$2 \times t_{\text{SYS}}$	—	ns
S2	I2S_MCLK pulse width high/low	45%	55%	MCLK period
S3	I2S_BCLK cycle time	$5 \times t_{\text{SYS}}$	—	ns
S4	I2S_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_BCLK to I2S_FS output valid	—	15	ns
S6	I2S_BCLK to I2S_FS output invalid	-4.3	—	ns
S7	I2S_BCLK to I2S_TXD valid	—	15	ns
S8	I2S_BCLK to I2S_TXD invalid	-4.6	—	ns
S9	I2S_RXD/I2S_FS input setup before I2S_BCLK	23.9	—	ns
S10	I2S_RXD/I2S_FS input hold after I2S_BCLK	0	—	ns

Table 49. I²S slave mode timing (full voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S11	I ² S_BCLK cycle time (input)	8 x t _{SYS}	—	ns
S12	I ² S_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I ² S_FS input setup before I ² S_BCLK	10	—	ns
S14	I ² S_FS input hold after I ² S_BCLK	3.5	—	ns
S15	I ² S_BCLK to I ² S_TXD/I ² S_FS output valid	—	28.6	ns
S16	I ² S_BCLK to I ² S_TXD/I ² S_FS output invalid	0	—	ns
S17	I ² S_RXD setup before I ² S_BCLK	10	—	ns
S18	I ² S_RXD hold after I ² S_BCLK	2	—	ns

6.9 Human-machine interfaces (HMI)

6.9.1 TSI electrical specifications

Table 50. TSI electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V _{DDTSI}	Operating voltage	1.71	—	3.6	V	
C _{ELE}	Target electrode capacitance range	1	20	500	pF	1
f _{REFmax}	Reference oscillator frequency	—	5.5	12.7	MHz	2
f _{ELEmax}	Electrode oscillator frequency	—	0.5	4.0	MHz	3
C _{REF}	Internal reference capacitor	0.5	1	1.2	pF	
V _{DELTA}	Oscillator delta voltage	100	600	760	mV	4
I _{REF}	Reference oscillator current source base current • 1uA setting (REFCHRG=0) • 32uA setting (REFCHRG=31)	— —	1.133 36	1.5 50	μA	3 , 5
I _{ELE}	Electrode oscillator current source base current • 1uA setting (EXTCHRG=0) • 32uA setting (EXTCHRG=31)	— —	1.133 36	1.5 50	μA	3 , 6
Pres5	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	7
Pres20	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	8
Pres100	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	9
MaxSens	Maximum sensitivity	0.003	12.5	—	fF/count	10
Res	Resolution	—	—	16	bits	
T _{Con20}	Response time @ 20 pF	8	15	25	μs	11
I _{TSI_RUN}	Current added in run mode	—	55	—	μA	
I _{TSI_LP}	Low power mode current adder	—	1.3	2.5	μA	12

1. The TSI module is functional with capacitance values outside this range. However, optimal performance is not guaranteed.
2. CAPTRM=7, DELVOL=7, and fixed external capacitance of 20 pF.

144 LQFP	144 MAP BGA	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
52	K6	PTA2	JTAG_TDO/ TRACE_SWO/ EZP_DO	TSIO_CH3	PTA2	UART0_TX	FTM0_CH7				JTAG_TDO/ TRACE_SWO	EZP_DO
53	K7	PTA3	JTAG_TMS/ SWD_DIO	TSIO_CH4	PTA3	UART0_RTS_ b	FTM0_CH0				JTAG_TMS/ SWD_DIO	
54	L7	PTA4/ LLWU_P3	NMI_b/ EZP_CS_b	TSIO_CH5	PTA4/ LLWU_P3		FTM0_CH1				NMI_b	EZP_CS_b
55	M8	PTA5	DISABLED		PTA5		FTM0_CH2		CMP2_OUT	I2S0_RX_ BCLK	JTAG_TRST	
56	E7	VDD	VDD	VDD								
57	G7	VSS	VSS	VSS								
58	J7	PTA6	DISABLED		PTA6		FTM0_CH3				TRACE_ CLKOUT	
59	J8	PTA7	ADC0_SE10	ADC0_SE10	PTA7		FTM0_CH4				TRACE_D3	
60	K8	PTA8	ADC0_SE11	ADC0_SE11	PTA8		FTM1_CH0			FTM1_QD_ PHA	TRACE_D2	
61	L8	PTA9	DISABLED		PTA9		FTM1_CH1			FTM1_QD_ PHB	TRACE_D1	
62	M9	PTA10	DISABLED		PTA10		FTM2_CH0			FTM2_QD_ PHA	TRACE_D0	
63	L9	PTA11	DISABLED		PTA11		FTM2_CH1			FTM2_QD_ PHB		
64	K9	PTA12	CMP2_IN0	CMP2_IN0	PTA12	CAN0_TX	FTM1_CH0			I2S0_TXD	FTM1_QD_ PHA	
65	J9	PTA13/ LLWU_P4	CMP2_IN1	CMP2_IN1	PTA13/ LLWU_P4	CAN0_RX	FTM1_CH1			I2S0_TX_FS	FTM1_QD_ PHB	
66	L10	PTA14	DISABLED		PTA14	SPI0_PCS0	UART0_TX			I2S0_TX_ BCLK		
67	L11	PTA15	DISABLED		PTA15	SPI0_SCK	UART0_RX			I2S0_RXD		
68	K10	PTA16	DISABLED		PTA16	SPI0_SOUT	UART0_CTS_ b			I2S0_RX_FS		
69	K11	PTA17	ADC1_SE17	ADC1_SE17	PTA17	SPI0_SIN	UART0_RTS_ b			I2S0_MCLK	I2S0_CLKIN	
70	E8	VDD	VDD	VDD								
71	G8	VSS	VSS	VSS								
72	M12	PTA18	EXTAL	EXTAL	PTA18		FTM0_FLT2	FTM_CLKIN0				
73	M11	PTA19	XTAL	XTAL	PTA19		FTM1_FLT0	FTM_CLKIN1		LPT0_ALT1		
74	L12	RESET_b	RESET_b	RESET_b								
75	K12	PTA24	DISABLED		PTA24					FB_A29		
76	J12	PTA25	DISABLED		PTA25					FB_A28		
77	J11	PTA26	DISABLED		PTA26					FB_A27		
78	J10	PTA27	DISABLED		PTA27					FB_A26		
79	H12	PTA28	DISABLED		PTA28					FB_A25		
80	H11	PTA29	DISABLED		PTA29					FB_A24		

Revision History

	1	2	3	4	5	6	7	8	9	10	11	12	
A	PTD7	PTD6	PTD5	PTD4	PTD0	PTC16	PTC12	PTC8	PTC4	NC	PTC3	PTC2	A
B	PTD12	PTD11	PTD10	PTD3	PTC19	PTC15	PTC11	PTC7	PTD9	NC	PTC1	PTC0	B
C	PTD15	PTD14	PTD13	PTD2	PTC18	PTC14	PTC10	PTC6	PTD8	NC	PTB23	PTB22	C
D	PTE2	PTE1	PTE0	PTD1	PTC17	PTC13	PTC9	PTC5	PTB21	PTB20	PTB19	PTB18	D
E	PTE6	PTE5	PTE4	PTE3	VDD	VDD	VDD	VDD	PTB17	PTB16	PTB11	PTB10	E
F	PTE10	PTE9	PTE8	PTE7	VDD	VSS	VSS	VDD	PTB9	PTB8	PTB7	PTB6	F
G	VOOUT33	VREGIN	PTE12	PTE11	VREFH	VREFL	VSS	VSS	PTB5	PTB4	PTB3	PTB2	G
H	USB0_DP	USB0_DM	VSS	PTE28	VDDA	VSSA	VSS	VSS	PTB1	PTB0	PTA29	PTA28	H
J	ADC0_DP1	ADC0_DM1	ADC0_SE16/ CMP1_IN2/ ADC0_SE21	PTE27	PTA0	PTA1	PTA6	PTA7	PTA13	PTA27	PTA26	PTA25	J
K	ADC1_DP1	ADC1_DM1	ADC1_SE16/ CMP2_IN2/ ADC0_SE22	PTE26	PTE25	PTA2	PTA3	PTA8	PTA12	PTA16	PTA17	PTA24	K
L	PGA0_DP/ ADC0_DP0/ ADC1_DP3	PGA0_DM/ ADC0_DM0/ ADC1_DM3	DAC0_OUT/ CMP1_IN3/ ADC0_SE23	DAC1_OUT/ CMP2_IN3/ ADC1_SE23	RESERVED	VBAT	PTA4	PTA9	PTA11	PTA14	PTA15	RESET_b	L
M	PGA1_DP/ ADC1_DP0/ ADC0_DP3	PGA1_DM/ ADC1_DM0/ ADC0_DM3	VREF_OUT/ CMP1_IN5/ CMP0_IN5/ ADC1_SE18	PTE24	NC	EXTAL32	XTAL32	PTA5	PTA10	VSS	PTA19	PTA18	M
	1	2	3	4	5	6	7	8	9	10	11	12	

Figure 28. K20 144 MAPBGA Pinout Diagram

9 Revision History

The following table provides a revision history for this document.

Table 51. Revision History

Rev. No.	Date	Substantial Changes
1	11/2010	Initial public revision

Table continues on the next page...

Table 51. Revision History (continued)

Rev. No.	Date	Substantial Changes
6	01/2012	- Added AC electrical specifications. - Replaced TBDs with silicon data throughout. - In "Power mode transition operating behaviors" table, removed entry times. - Updated "EMC radiated emissions operating behaviors" to remove SAE level and also added data for 144LQFP. - Clarified "EP7" in "EzPort switching specifications" table and "EzPort Timing Diagram". - Added "ENOB vs. ADC_CLK for 16-bit differential and 16-bit single-ended modes" figures. - Updated I_{DD_RUN} numbers in 'Power consumption operating behaviors' section. - Clarified 'Diagram: Typical I_{DD_RUN} operating behavior' section and updated 'Run mode supply current vs. core frequency — all peripheral clocks disabled' figure. - In 'Voltage reference electrical specifications' section, updated C_L, V_{tdrift}, and V_{vdift} values. - In 'USB electrical specifications' section, updated V_{DP_SRC}, I_{DDstby}, and '$V_{Reg33out}$' values.
7	02/2013	- In "ESD handling ratings", added a note for I_{LAT}. - Updated "Voltage and current operating requirements". - Updated "Voltage and current operating behaviors". - Updated "Power mode transition operating behaviors". - Updated "EMC radiated emissions operating behaviors" to add MAPBGA data. - In "MCG specifications", updated the description of f_{ints_t}. - In "16-bit ADC operating conditions", updated the max spec of V_{ADIN}. - In "16-bit ADC electrical characteristics", updated the temp sensor slope and voltage specs. - Updated "I2C switching specifications". - In "SDHC specifications", removed the operating voltage limits and updated the SD1 and SD6 specs. - In "I2S switching specifications", added separate specification tables for the full operating voltage range.